NEC

MOS FIELD EFFECT TRANSISTOR
μPA1772

SWITCHING
P-CHANNEL POWER MOS FET

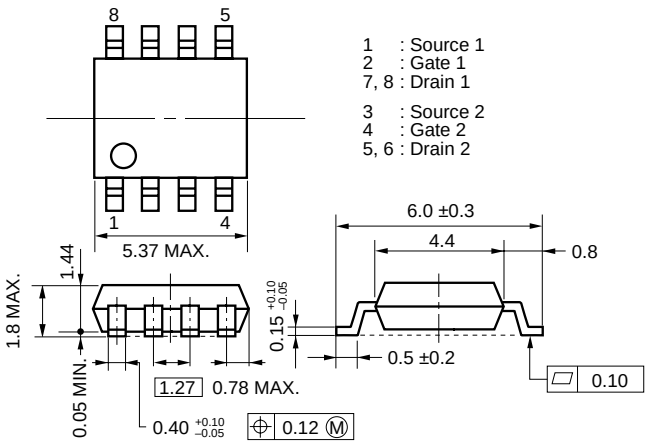
DESCRIPTION

The μPA1772 is Dual P-Channel MOS Field Effect Transistor designed for power management applications of portable machines.

FEATURES

- Dual chip type
- Low on-state resistance
  $R_{DS(on)1}$ = 20.0 mΩ MAX. (V_{GS} = –10 V, I_D = –4 A)
  $R_{DS(on)2}$ = 29.5 mΩ MAX. (V_{GS} = –4.5 V, I_D = –4 A)
  $R_{DS(on)3}$ = 34.0 mΩ MAX. (V_{GS} = –4.0 V, I_D = –4 A)
- Low C_{iss}: C_{iss} = 1500 pF TYP. (V_{DS} = –10 V, V_{GS} = 0 V)
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

PACKAGE DRAWING (Unit : mm)



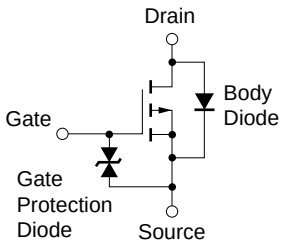
ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1772G	Power SOP8

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, All terminals are connected.)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	–30	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	∓20	V
Drain Current (DC)	$I_{D(DC)}$	∓8	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	∓32	A
Total Power Dissipation (2 unit) Note2	P_T	2.0	W
Total Power Dissipation (1 unit) Note2	P_T	1.7	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to + 150	°C

EQUIVALENT CIRCUIT
(1/2 circuit)



Notes 1. PW ≤ 10 μs, Duty cycle ≤ 1%

2. T_A = 25°C, Mounted on ceramic substrate of 2000 mm^2 x 2.2 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device..

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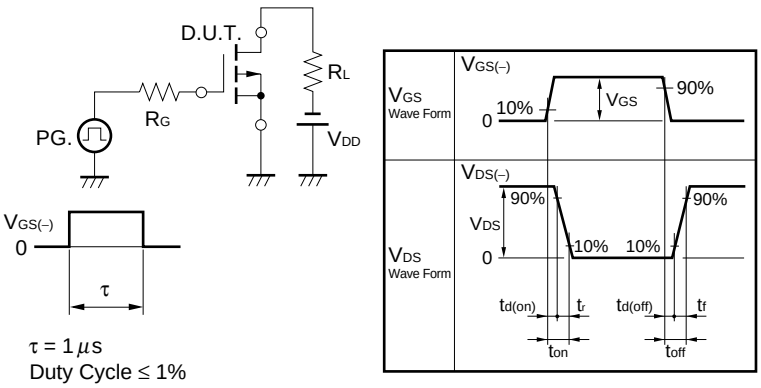
ELECTRICAL CHARACTERISTICS (T_A = 25°C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –30 V, V_{GS} = 0 V			–1	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ∓20 V, V_{DS} = 0 V			∓10	μA
Gate Cut-off Voltage Note	$V_{GS(off)}$	V_{DS} = –10 V, I_D = –1 mA	–1.0	–1.7	–2.5	V
Forward Transfer Admittance Note	$\|y_{fs}\|$	V_{DS} = –10 V, I_D = –4 A	6	12		S
Drain to Source On-state Resistance Note	$R_{DS(on)1}$	V_{GS} = –10 V, I_D = –4 A		17.4	20.0	mΩ
	$R_{DS(on)2}$	V_{GS} = –4.5 V, I_D = –4 A		23.5	29.5	mΩ
	$R_{DS(on)3}$	V_{GS} = –4.0 V, I_D = –4 A		25.8	34.0	mΩ
Input Capacitance	C_{iss}	V_{DS} = –10 V		1500		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		550		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		240		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = –15 V, I_D = –4 A		13		ns
Rise Time	t_r	V_{GS} = –10 V		11		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		120		ns
Fall Time	t_f			70		ns
Total Gate Charge	Q_G	V_{DD} = –24 V		34		nC
Gate to Source Charge	Q_{GS}	V_{GS} = –10 V		5		nC
Gate to Drain Charge	Q_{GD}	I_D = –8 A		9		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 8 A, V_{GS} = 0 V		0.84	1.2	V
Reverse Recovery Time	t_{rr}	I_F = 8 A, V_{GS} = 0 V		50		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		37		nC

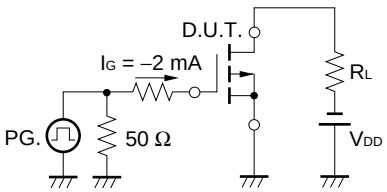
Note Pulsed: PW ≤ 350 μs, Duty cycle ≤ 2%

TEST CIRCUIT 1 SWITCHING TIME



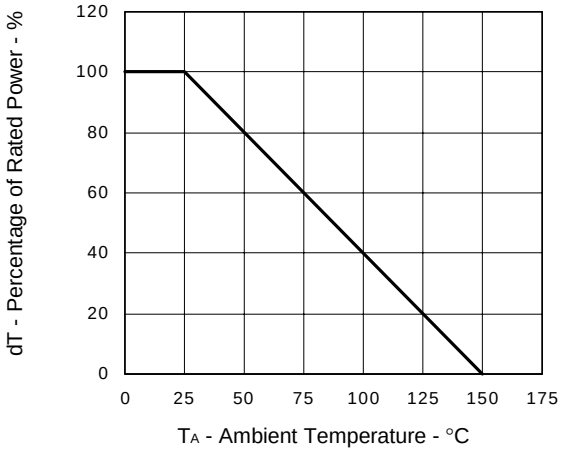
τ = 1 μs
Duty Cycle ≤ 1%

TEST CIRCUIT 2 GATE CHARGE

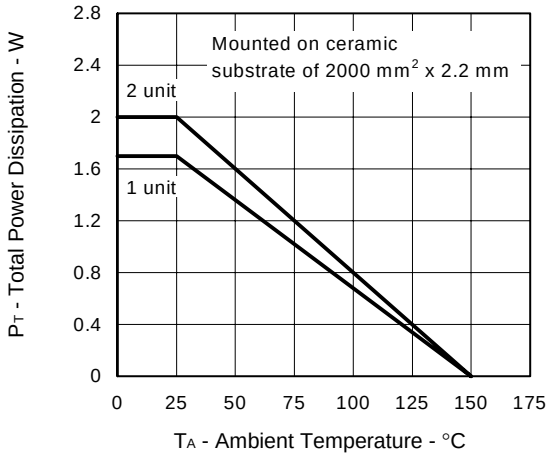


TYPICAL CHARACTERISTICS (T_A = 25°C)

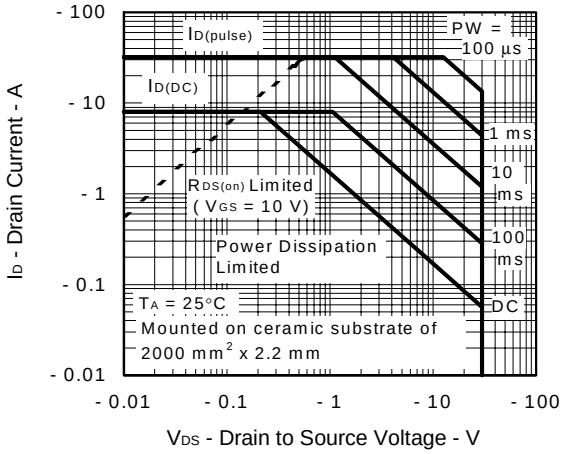
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



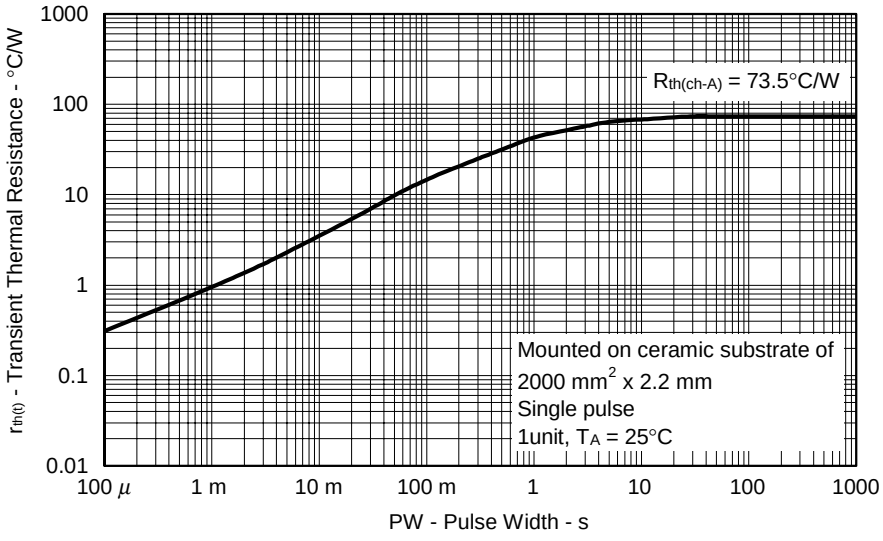
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



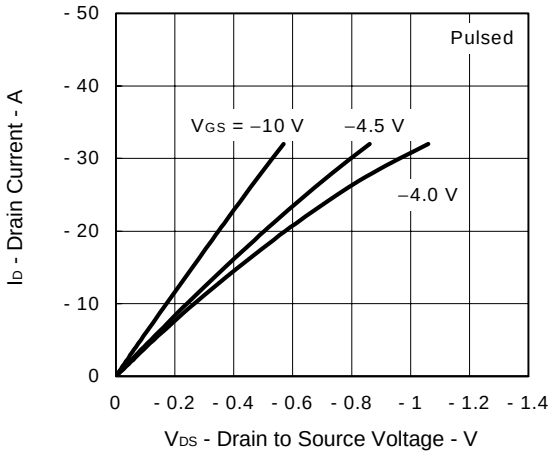
FORWARD BIAS SAFE OPERATING AREA



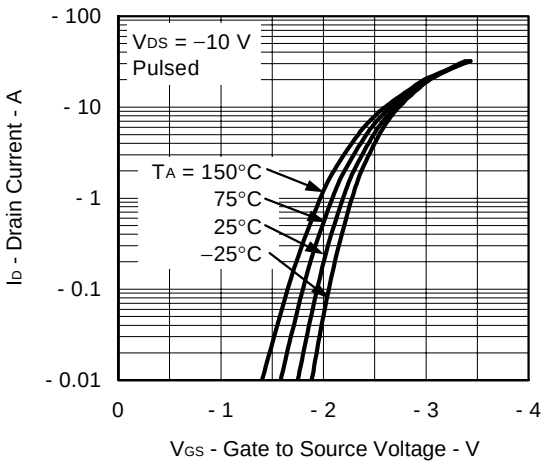
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



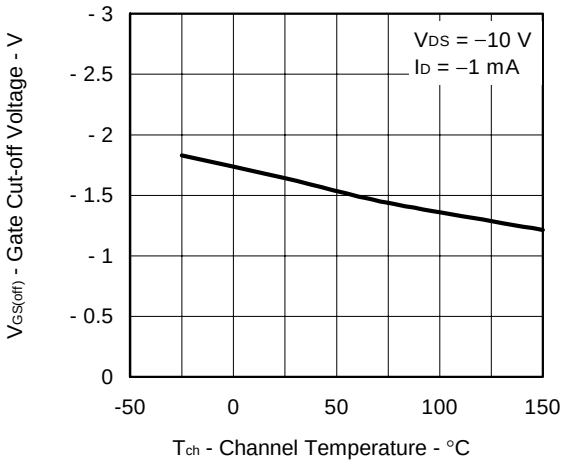
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



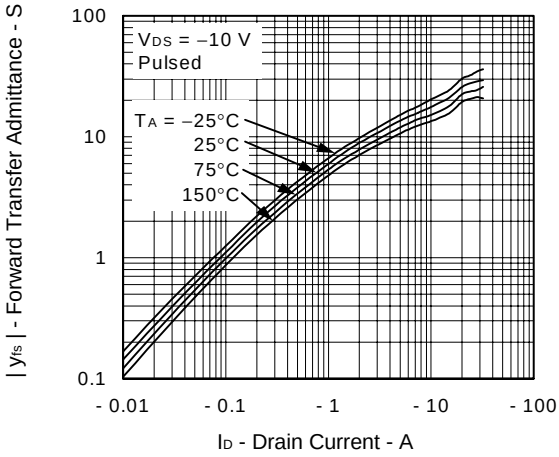
FORWARD TRANSFER CHARACTERISTICS



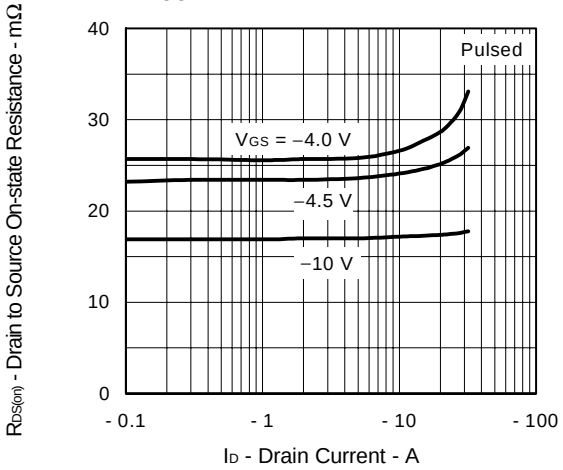
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



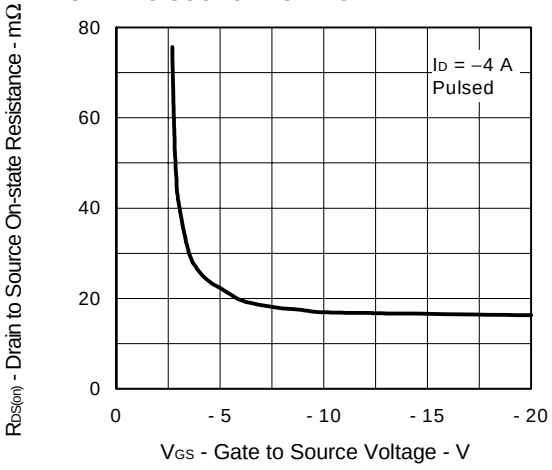
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



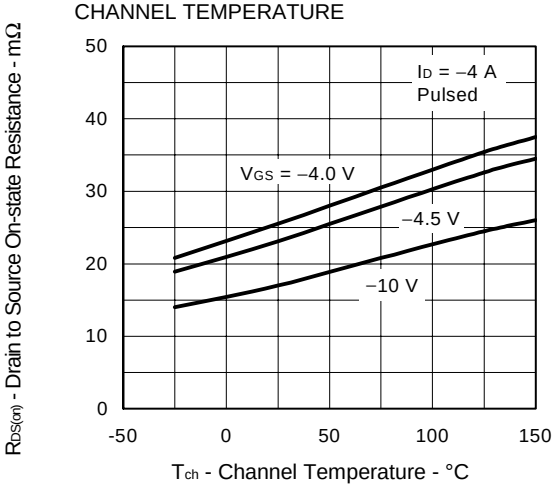
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



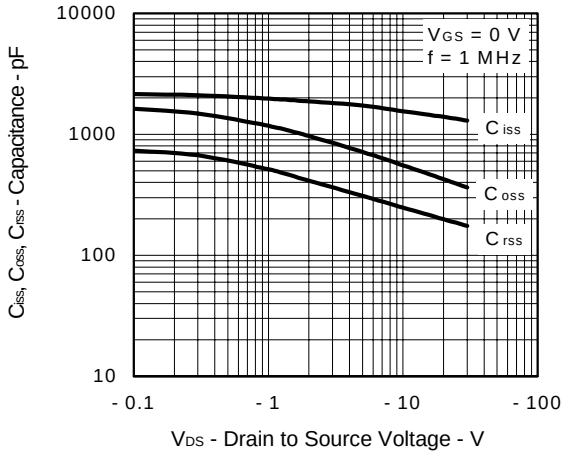
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



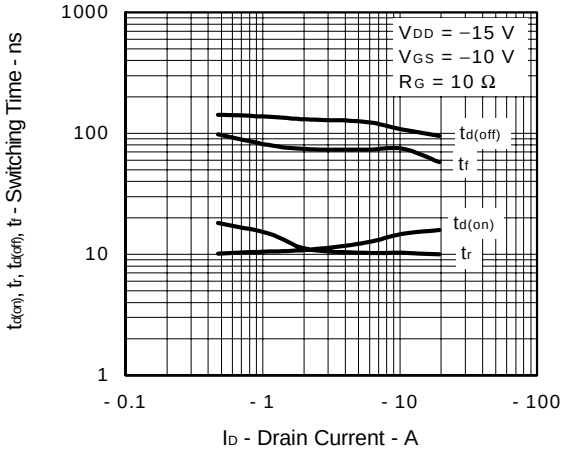
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



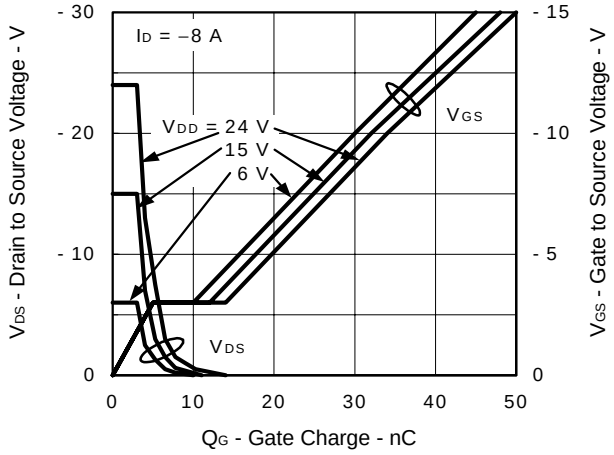
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



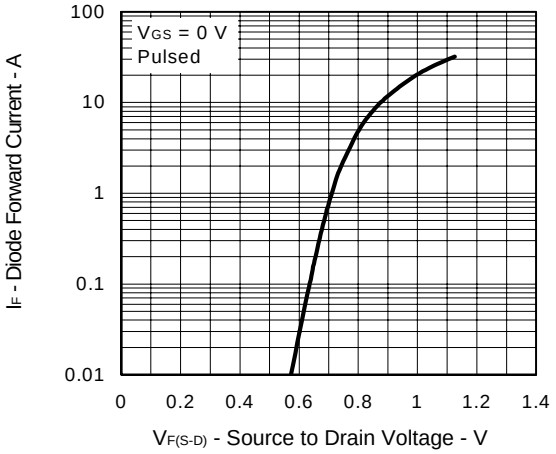
SWITCHING CHARACTERISTICS



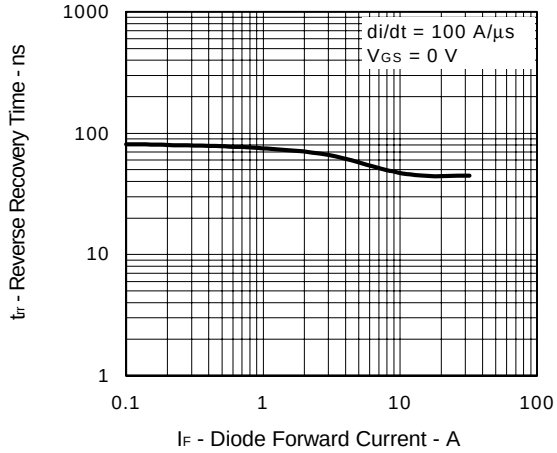
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



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